

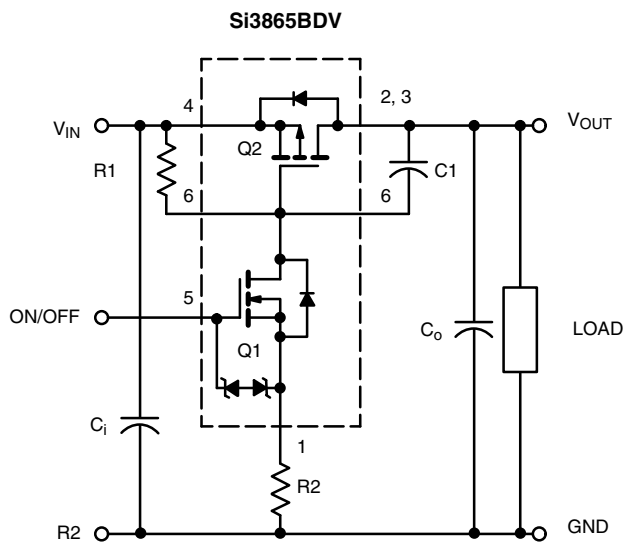
Load Switch with Level-Shift

PRODUCT SUMMARY		
V_{DS2} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
1.8 to 8	0.060 at $V_{IN} = 4.5$ V	2.9
	0.100 at $V_{IN} = 2.5$ V	2.2
	0.175 at $V_{IN} = 1.8$ V	1.7

DESCRIPTION

The Si3865BDV includes a p- and n-channel MOSFET in a single TSOP-6 package. The low on-resistance p-channel TrenchFET[®] is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a level-shift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si3865BDV operates on supply lines from 1.8 V to 8 V, and can drive loads up to 2.9 A.

APPLICATION CIRCUITS



COMPONENTS		
R1	Pull-Up Resistor	Typical 10 k Ω to 1 M Ω *
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω *
C1	Optional Slew-Rate Control	Typical 1000 pF

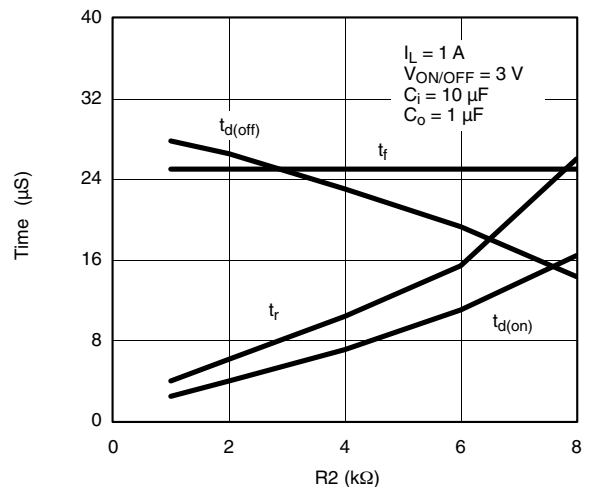
* Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- 60 m Ω Low $R_{DS(on)}$ TrenchFET[®]: 1.8 V Rated
- 1.8 V to 8 V Input
- 1.5 V to 8 V Logic Level Control
- Low Profile, Small Footprint TSOP-6 Package
- 3000 V ESD Protection On Input Switch, $V_{ON/OFF}$
- Adjustable Slew-Rate
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

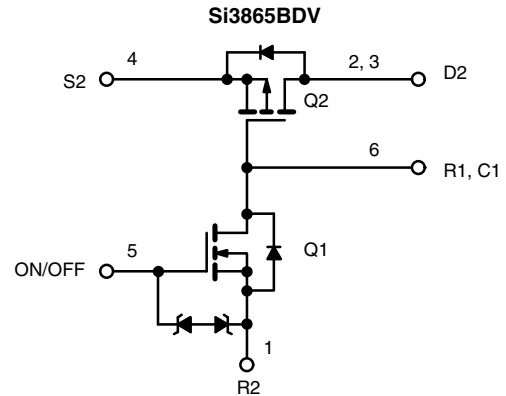
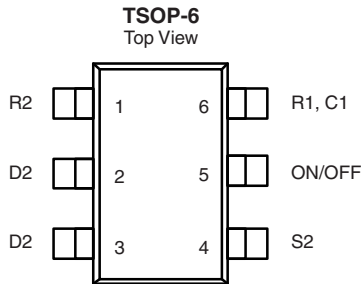


Note: For R2 switching variations with other $V_{IN}/R1$ combinations See Typical Characteristics

Switching Variation
R2 at $V_{IN} = 2.5$ V, $R1 = 20$ k Ω

The Si3865BDV is ideally suited for high-side load switching in portable applications. The integrated N-Channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

FUNCTIONAL BLOCK DIAGRAM



Ordering Information: Si3865BDV-T1-E3 (Lead (Pb)-free)
Si3865BDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Input Voltage	V _{IN}	8	V	
On/Off Voltage	V _{ON/OFF}	8		
Load Current	Continuous ^{a, b}	± 2.9	A	
	Pulsed ^{b, c}	± 6		
Continuous Intrinsic Diode Conduction ^a	I _S	- 1		
Maximum Power Dissipation ^a	P _D	0.83	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)	ESD	3	kV	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (continuous current) ^a	R _{thJA}	125	150	°C/W
Maximum Junction-to-Foot (Q2)	R _{thJC}	40	55	

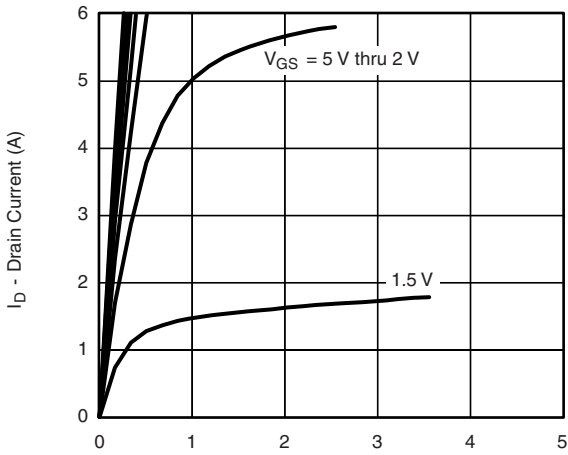
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Reverse Leakage Current	I _{FL}	V _{IN} = 8 V, V _{ON/OFF} = 0 V			1	μA
Diode Forward Voltage	V _{SD}	I _S = - 1 A		- 0.77	- 1	V
OnN Characteristics						
Input Voltage Range	V _{IN}		1.8		8	V
On-Resistance (P-Channel) at 1 A	R _{DS(on)}	V _{ON/OFF} = 1.5 V, I _D = 1 A	V _{IN} = 4.5 V	0.045	0.060	Ω
			V _{IN} = 2.5 V	0.075	0.100	
			V _{IN} = 1.8 V	0.135	0.175	
On-State (P-Channel) Drain-Current	I _{D(on)}	V _{IN-OUT} ≤ 0.2 V, V _{IN} = 5 V, V _{ON/OFF} = 1.5 V	1			A
		V _{IN-OUT} ≤ 0.3 V, V _{IN} = 3 V, V _{ON/OFF} = 1.5 V	1			

Notes:

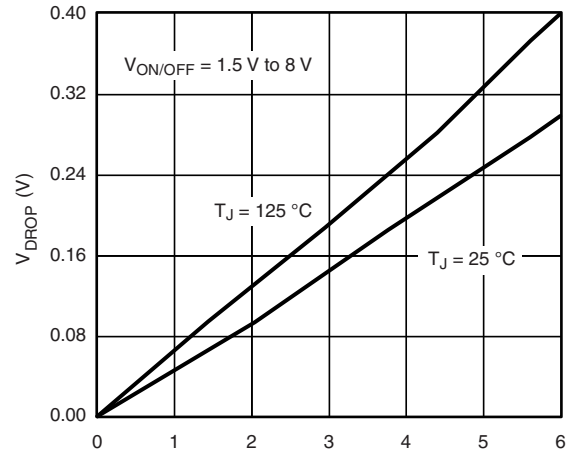
- a. Surface Mounted on FR4 board.
- b. V_{IN} = 8 V, V_{ON/OFF} = 8 V, T_A = 25 °C.
- c. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

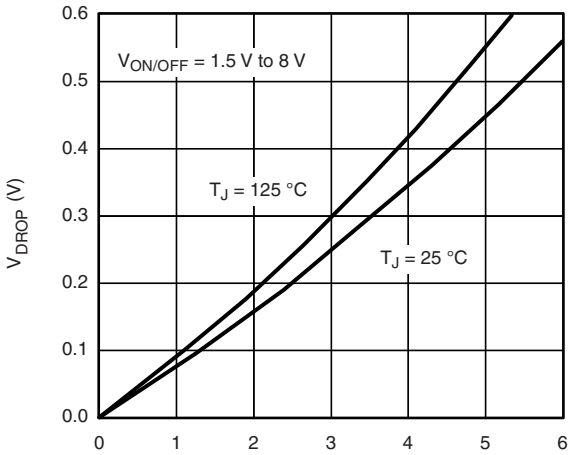
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



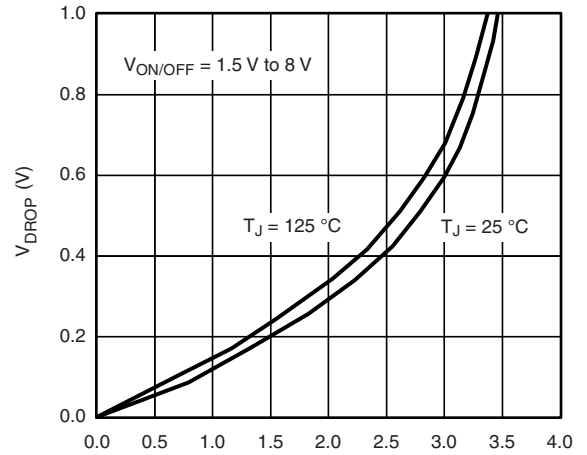
Output Characteristics



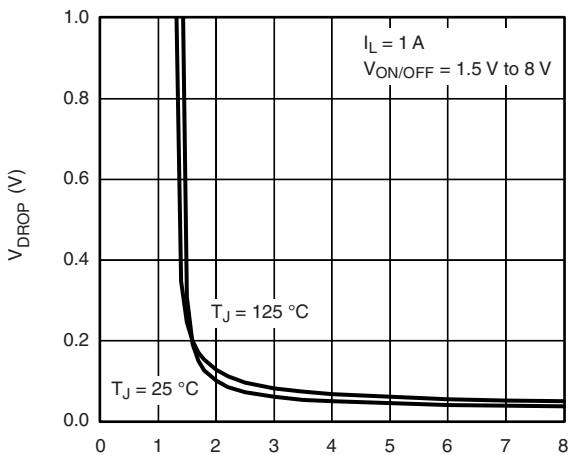
V_{DROP} vs. I_L at $V_{IN} = 4.5$ V



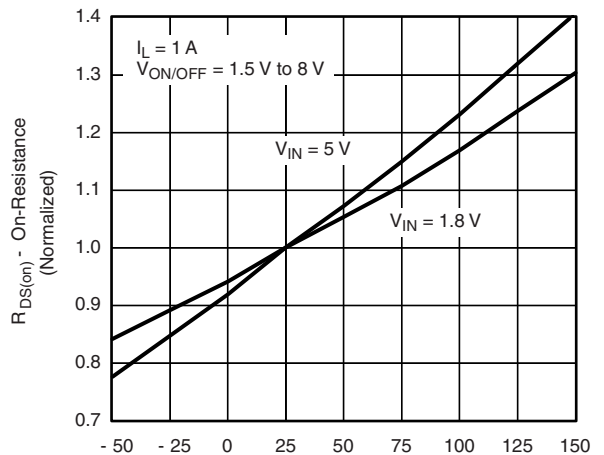
V_{DROP} vs. I_L at $V_{IN} = 2.5$ V



V_{DROP} vs. I_L at $V_{IN} = 1.8$ V

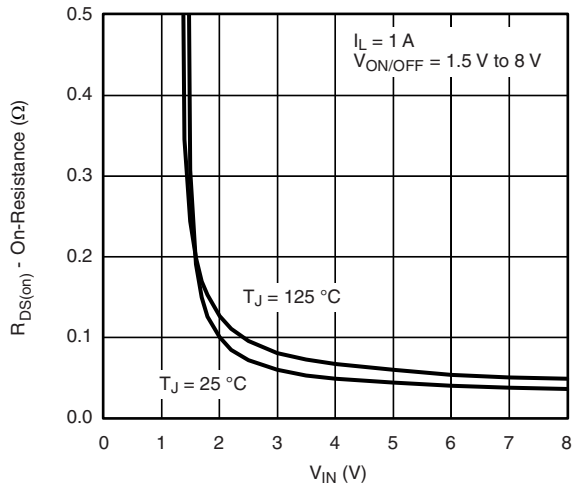


V_{DROP} vs. V_{IN} at $I_L = 1$ A

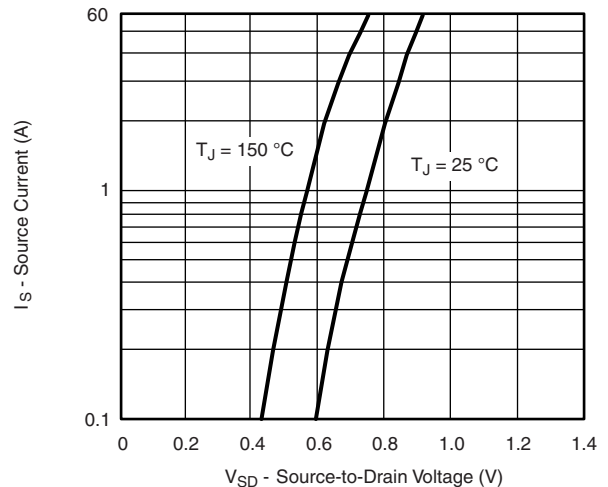


Normalized On-Resistance vs. Junction Temperature

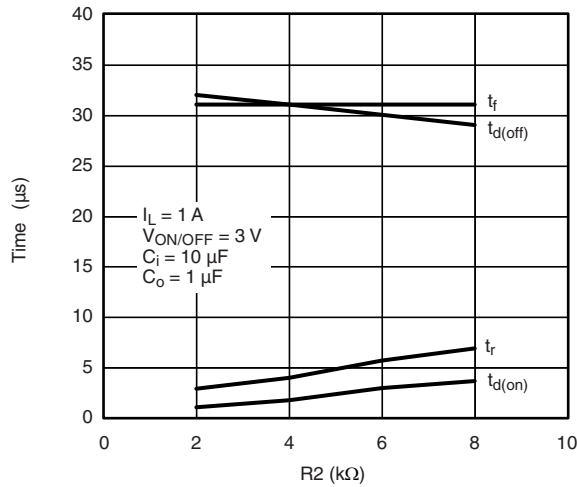
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



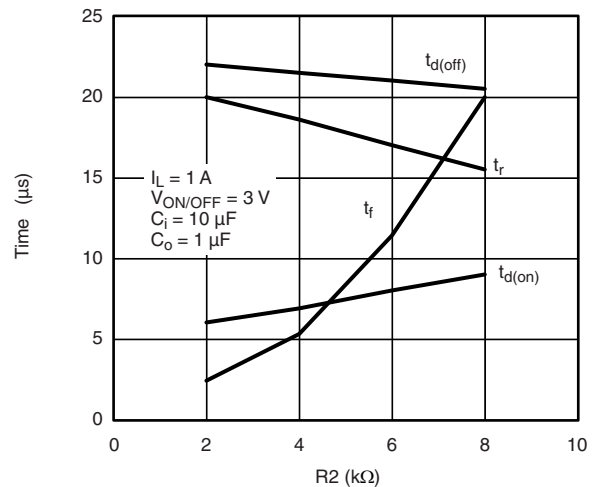
On-Resistance vs. Input Voltage



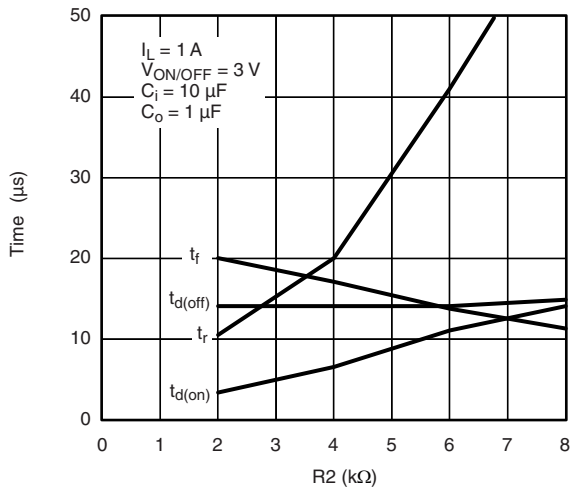
Source-Drain Diode Forward Voltage



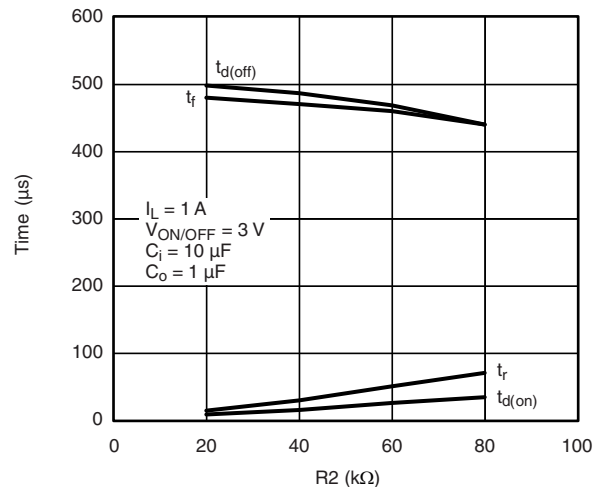
Switching Variation
R2 at $V_{IN} = 4.5\text{ V}$, $R_1 = 20\text{ k}\Omega$



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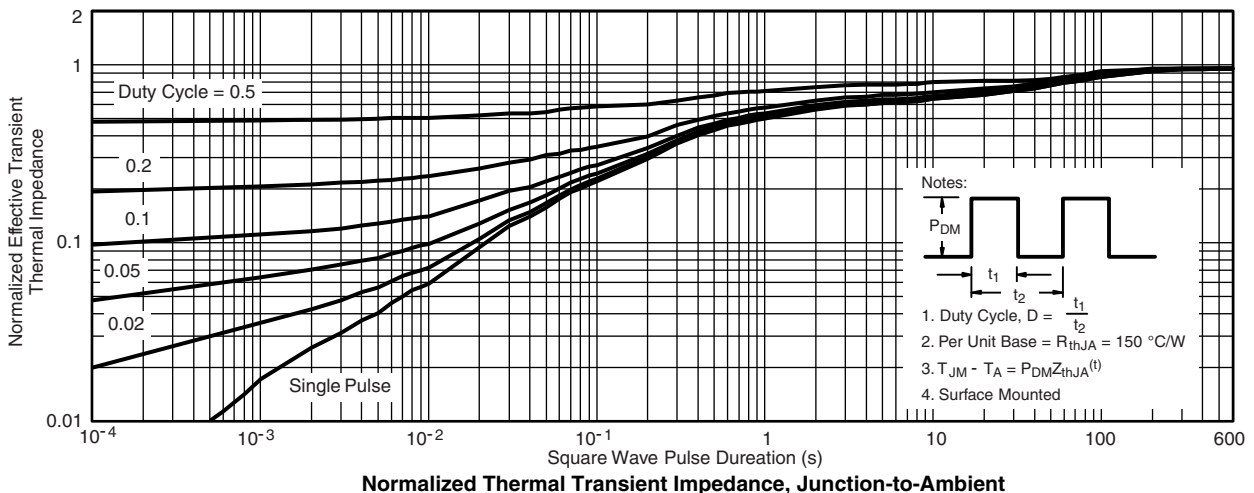
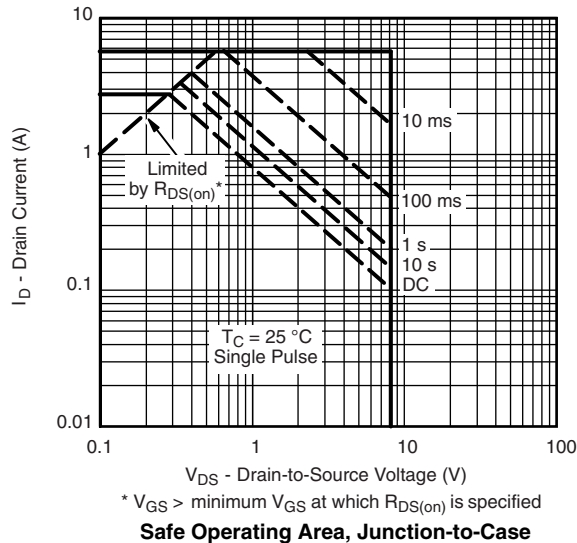
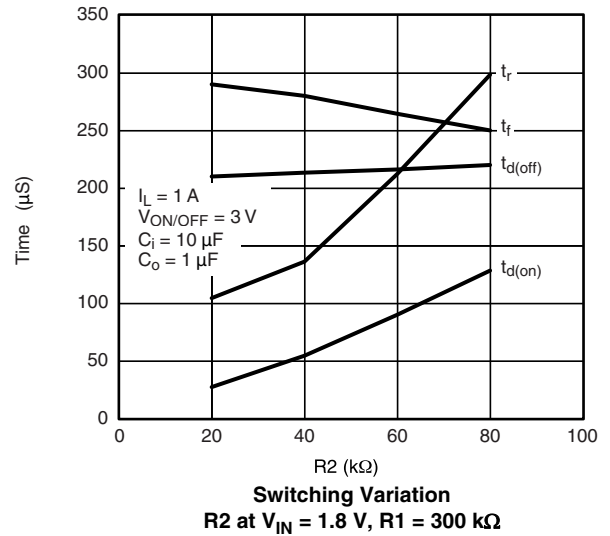
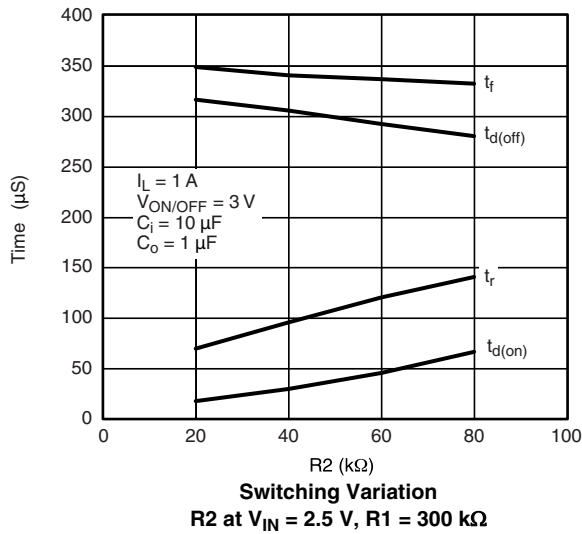


Switching Variation
R2 at $V_{IN} = 1.8\text{ V}$, $R_1 = 20\text{ k}\Omega$



Switching Variation
R2 at $V_{IN} = 4.5\text{ V}$, $R_1 = 300\text{ k}\Omega$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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